

Magnetoresistance effect device, and magnetoresistance effect type head, memory device, and amplifying device using the same**Publication number:** CN1121252**Publication date:** 1996-04-24**Inventor:** SAKAMINA HIROSHI (JP); IRIE YOUSUKE (JP); SATOMI MITSUO (JP)**Applicant:** MATSUSHITA ELECTRIC IND CO LTD (JP)**Classification:**

- International: G01R33/09; G11B5/39; G11C11/15; G11C11/16; G11C11/56; H01L21/8246; H01L27/22; H01L43/10; H03F7/02; G01R33/06; G11B5/39; G11C11/02; G11C11/56; H01L21/77; H01L27/22; H01L43/00; H03F7/00;

- European: G01R33/09B; G11B5/39C; G11C11/15; G11C11/16; G11C11/56B; H01L21/8246M; H01L27/22; H01L43/10; H03F7/02; Y01N4/00; Y01N12/00

Application number: CN19951006521 19950502**Priority number(s):** JP19940093257 19940502; JP19950053067 19950313; JP19940125072 19940607; JP19940149229 19940630; JP19940176822 19940728; JP19940178078 19940729; JP19940187484 19940809; JP19940190457 19940812; JP19940303615 19941207; JP19940313147 19941216; JP19950051630 19950310**Also published as:**

- EP0681338 (A1)
- US5841611 (A1)
- EP0681338 (B1)
- CN1126127C (C)

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Abstract not available for CN1121252

Abstract of corresponding document: EP0681338

A magnetoresistance effect device of the invention includes: a substrate; and a multilayer structure formed on the substrate. The multilayer structure includes a hard magnetic film, a soft magnetic film, and a non-magnetic metal film for separating the hard magnetic film from the soft magnetic film. The magnetization curve of the hard magnetic film has a good square feature, and the direction of a magnetization easy axis of the hard magnetic film substantially agrees to the direction of a magnetic field to be detected.

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